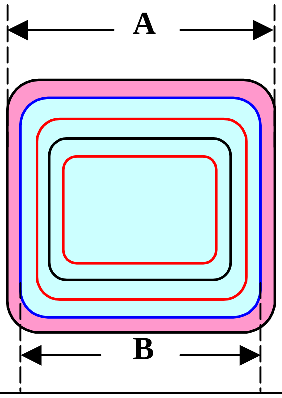
CMS-S040-040L

SCHOTTKY BARRIER DIODE

Features :

* Extremely low forward volts
* Guard ring protection
* Low reverse leakage current



Chip size(A):	1.016 * 1.016 mm^2
Bond Pad size(B) :	0.889 * 0.889 mm^2
Thickness :	300µm ± 20µm
Metalization :	Anode Ti/Ni/Ag
Metalization :	Cathode Ti/Ni/Ag

Electrical Characteristics	Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C	VF max	0.40	Volt
Minimum Instantaneous Reverse Voltage at IR : 300 uA 25°C	VR min.	43	Volt.
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	40	Amp
Storage Temperature	TSTG	-65 to +125	°C

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